# 捷多邦,专业PCB打样工厂,24小时加急出货

DG3015

Vishay Siliconix

## Low-Voltage, Low r<sub>ON</sub>, Dual DPDT Analog Switch

#### DESCRIPTION

VISHAY

The DG3015 is a dual double-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG3015 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG3015 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-beforemake is guaranteed.

The switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

#### **FEATURES**

- Low Voltage Operation (2.7 V to 3.3 V)
- Low On-Resistance r<sub>ON</sub>: 0.80 Ω
- 3 dB Loss at 100 MHz
- Fast Switching: t<sub>ON</sub> = 40 ns t<sub>OFF</sub> = 35 ns
- MICRO FOOT<sup>®</sup> Package

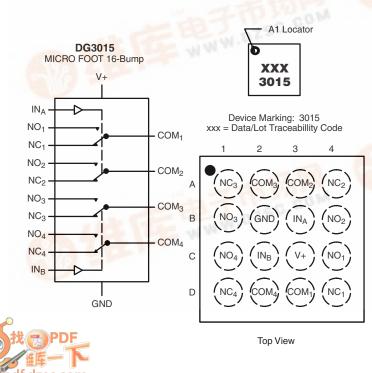
#### BENEFITS

- Reduced Power Consumption W.DZSC.
- High Accuracy
- Reduce Board Space
- TTL/1.8 V Logic Compatible
- High Bandwidth

#### **APPLICATIONS**

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- PCMCIA Cards
- WWW.DZSC.COM **Battery Operated Systems**

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE					
Logic	NC1, 2, 3 and 4	NO1, 2, 3 and 4			
0	ON	OFF			
1	OFF	ON			

ORDERING INFORMATION					
Temp Range	Package	Part Number			
- 40 to 85 °C	MICRO FOOT: 16 Bump (4 x 4, 0.5 mm Pitch, 238 µm Bump Height)	DG3015DB-T2-E1			



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<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25 \text{ °C}$ , unless otherwise noted					
Parameter	Limit	Unit			
Reference V+ to GND	- 0.3 to + 6	V			
IN, COM, NC, NO <sup>a</sup>	- 0.3 to (V+ + 0.3 V)	v			
Current (Any terminal except NO, NC or	30				
Continuous Current (NO, NC or COM)	± 150	mA			
Peak Current (Pulsed at 1 ms, 10 % duty	± 250				
Storage Temperature	(D Suffix)	- 65 to 150			
Package Solder Reflow Conditions <sup>b</sup>	IR/Convection	250	°C		
Power Dissipation (Packages) <sup>c</sup>	MICRO FOOT: 16 Bump (4 x 4 mm) <sup>d</sup>	719	mW		

Notes: a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. Refer to IPC/JEDEC (J-STD-020B) c. All bumps welded or soldered to PC Board. d. Derate 9.0 mW/°C above 70 °C.

Permanent damage to the device may occur when the "Absolute Maximum Ratings" are exceeded. These stress ratings do not indicate conditions for which the device is intended to be functional. Functionality is only guaranteed to the conditions specified by the parametric table within the document.

SPECIFICATIONS (V+ = 3 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C			
Parameter	Symbol	V+ = 3 V, $\pm$ 10 %,V_{IN} = 0.4 V or 2.0 V $^{e}$	Temp <sup>a</sup>	Min <sup>b</sup>	Тур <sup>с</sup>	Max <sup>b</sup>	Unit
Analog Switch				•	•	•	
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>		Full	0		V+	V
On-Resistance	r <sub>ON</sub>	V+ = 2.7 V, V <sub>COM</sub> = 0.2 V/1.5 V I <sub>NO</sub> , I <sub>NC</sub> = 100 mA	Room Full		0.80	1.2 1.3	
r <sub>ON</sub> Flatness	r <sub>ON</sub> Flatness	$V_{+} = 2.7 V, V_{COM} = 0 \text{ to } V_{+},$ $I_{NO}, I_{NC} = 100 \text{ mA}$	Room		0.16		Ω
r <sub>ON</sub> Match	$\Delta r_{ON}$		Room		0.15		
Switch Off Leakage Current	I <sub>NO(off)</sub> I <sub>NC(off)</sub>	V+ = 3.3 V,	Room Full	- 2 - 20		2 20	
Switch On Esakage Suitchik	I <sub>COM(off)</sub>	$V_{NO}$ , $V_{NC}$ = 1 V/3 V, $V_{COM}$ = 3 V/1 V		- 2 - 20		2 20	nA
Channel-On Leakage Current	I <sub>COM(on)</sub>	V+ = 3.3 V, V <sub>NO</sub> , V <sub>NC</sub> = V <sub>COM</sub> = 1 V/3 V	Room Full	- 2 - 20		2 20	
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	2			v
Input Low Voltage	V <sub>INL</sub>		Full			0.4	
Input Capacitance	C <sub>in</sub>		Full		4		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	$V_{IN} = 0$ or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t <sub>ON</sub>		Room Full		40	65 67	
Turn-Off Time	t <sub>OFF</sub>	$V_{NO}$ or $V_{NC}$ = 2.0 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room Full		35	60 62	ns
Break-Before-Make Time	t <sub>d</sub>		Full	1	3		
Charge Injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L$ = 1 nF, $V_{GEN}$ = 0 V, $R_{GEN}$ = 0 $\Omega$	Room		7		рС
Off-Isolation <sup>d</sup>	OIRR	R <sub>I</sub> = 50 Ω, C <sub>I</sub> = 5 pF, f = 1 MHz	Room		- 67		dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>		Room		- 70		
N <sub>O</sub> , N <sub>C</sub> Off Capacitance <sup>d</sup>	C <sub>NO(off)</sub>		Room		63		– pF
	C <sub>NC(off)</sub>	V <sub>IN</sub> = 0 or V+, f = 1 MHz	Room		67		
Channel-On Capacitance <sup>d</sup>	C <sub>NO(on)</sub>	$v_{\text{IN}} = 0.01$ $v_{\text{I}}$ , $v_{\text{I}} = 1.0012$	Room		200		, Pi
Chamber On Capacitance	C <sub>NC(on)</sub>		Room		196		



SPECIFICATIONS (V+ = 3 V)								
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C				
Parameter	Symbol	$V + = 3 V, \pm 10 \%, V_{IN} = 0.4 V \text{ or } 2.0 V^{e}$	Temp <sup>a</sup>	Min <sup>b</sup>	Typ <sup>c</sup>	Max <sup>b</sup>	Unit	
Power Supply								
Power Supply Range	V+			2.7		3.3	V	
Power Supply Current	l+	V <sub>IN</sub> = 0 or V+	Full			1.0	μA	

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

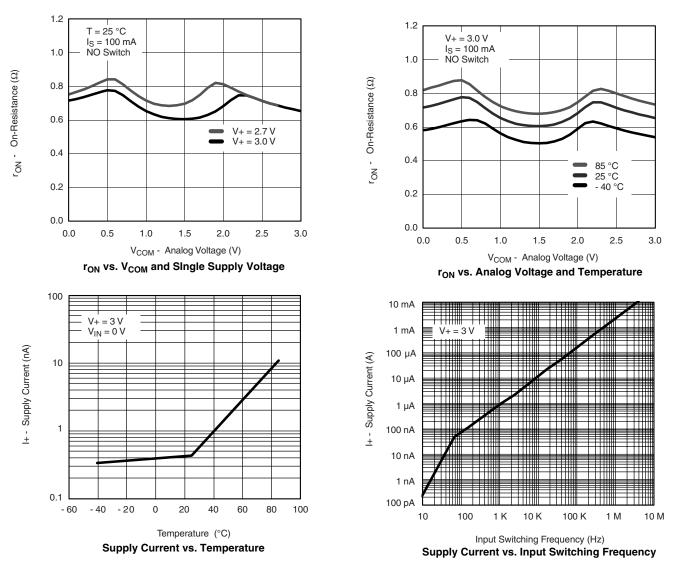
c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e.  $V_{IN}$  = input voltage to perform proper function.

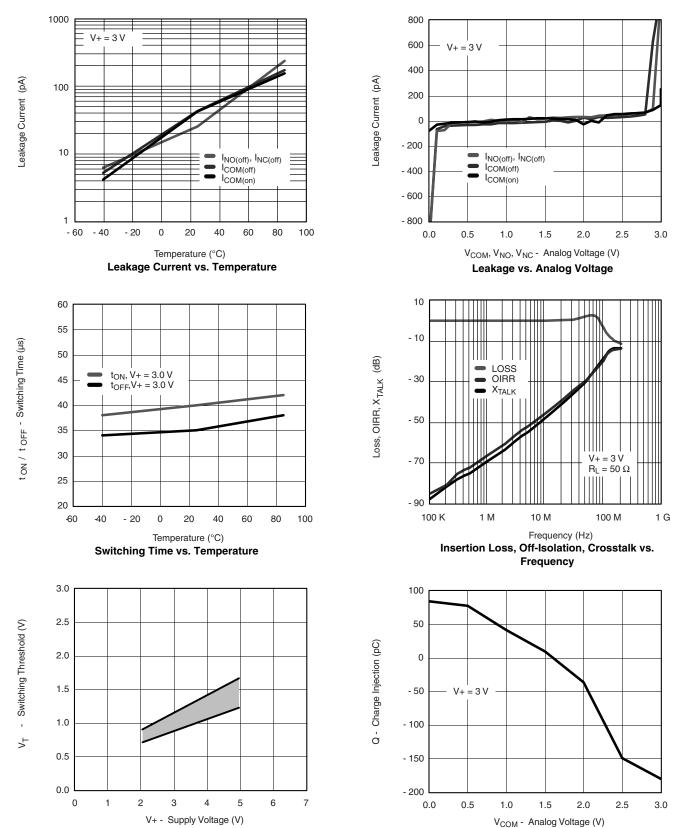
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Switching Threshold vs. Supply Voltage

Charge Injection vs. Analog Voltage





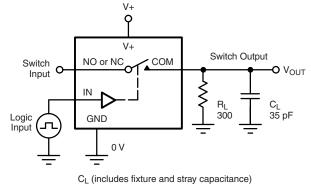
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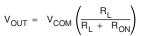
t<sub>r</sub> < 5 ns

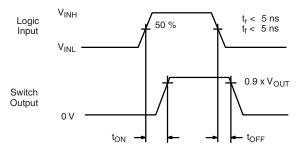
t<sub>f</sub> < 5 ns

tD

### **TEST CIRCUITS**







Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



Logic

Input

VINH

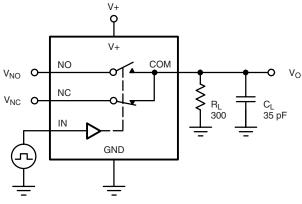
VINL

90 %

t<sub>D</sub>

 $V_{NC} = V_{NO}$  $V_{O}$ 

Switch Output 0 V



C<sub>L</sub> (includes fixture and stray capacitance)



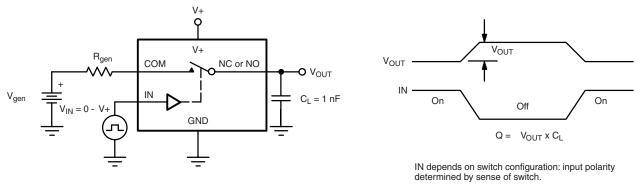


Figure 3. Charge Injection

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### **TEST CIRCUITS**

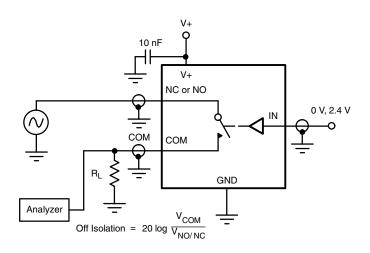


Figure 4. Off-Isolation

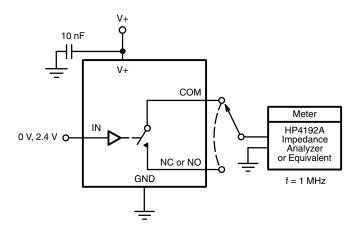
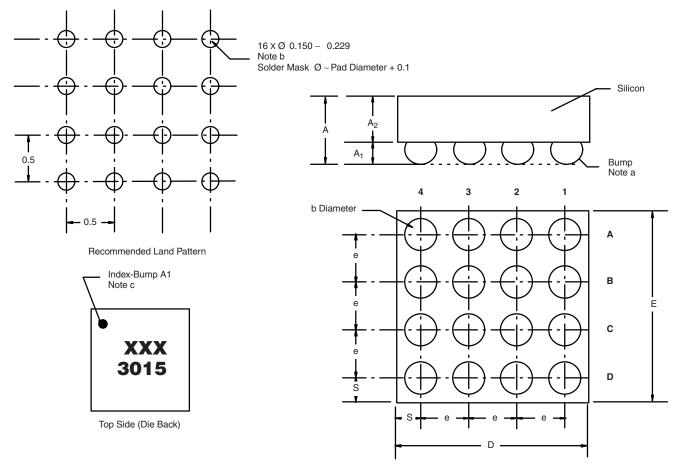


Figure 5. Channel Off/On Capacitance



### PACKAGE OUTLINE

### MICRO FOOT: 16 BUMP (4 x 4, 0.5 mm PITCH, 0.238 mm BUMP HEIGHT)



Notes (Unless Otherwise Specified):

a. Bump is Lead (Pb)-free Sn/Ag/Cu.

b. Non-solder mask defined copper landing pad.

c. Laser Mark on silicon die back; back-lapped, no coating. Shown is not actual marking; sample only.

Dim	Millimeters <sup>a</sup>		Inches		
Dilli	Min	Max	Min	Max	
Α	0.688	0.753	0.0271	0.0296	
A <sub>1</sub>	0.218	0.258	0.0086	0.0102	
A <sub>2</sub>	0.470	0.495	0.0185	0.0195	
b	0.306	0.346	0.0120	0.0136	
D	1.980	2.020	0.0780	0.0795	
E	1.980	2.020	0.0780	0.0795	
е	0.5 BASIC		0.0197	BASIC	
S	0.230	0.270	0.0091	0.0106	

Notes:

a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72962.



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